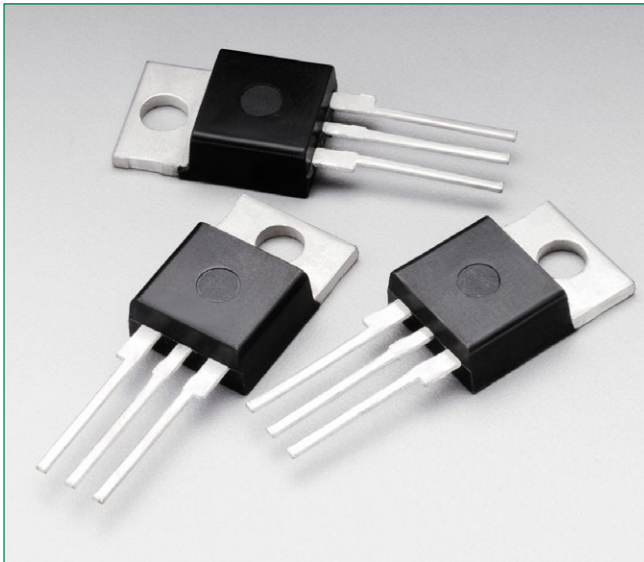


BTA16-600CW3G, BTA16-800CW3G,

RoHS



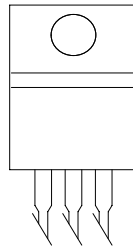
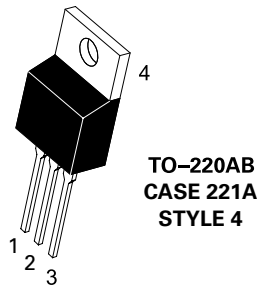
Description

Designed for high performance full-wave ac control applications where high noise immunity and high commutating di/dt are required.

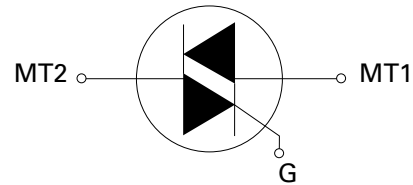
Features

- Blocking Voltage to 800 V
- On-State Current Rating of 16 A RMS at 25°C
- Uniform gate trigger for Quadrants I, II, and III.
- High Immunity to dv/dt – 1000 V/μs minimum at 125°C
- Minimizes Snubber Networks for Protection
- Industry Standard TO-220AB Package
- High Commutating di/dt – 8.5A/ms minimum at 125°C
- Internally Isolated (2500 V_{RMS})
- These components are Pb-Free and are RoHS Compliant

Pin Out



Schematic Symbol



Additional Information



Datasheet



Resources



Samples

Maximum Ratings ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (Gate Open, Sine Wave 50 to 60 Hz, $T_J = -40^\circ$ to 125°C)	BTA16-600CW3G BTA16-800CW3G V_{DRM}^* V_{RRM}	600 800	V
On-State RMS Current (Full Cycle Sine Wave, 60 Hz, $T_C = 80^\circ\text{C}$)	I_T (RMS)	12	A
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, $T_C = 25^\circ\text{C}$)	I_{TSM}	125	A
Circuit Fusing Consideration ($t = 8.3$ ms)	I^2t	78	A ² sec
Non-Repetitive Surge Peak Off-State Voltage ($T_J = 25^\circ\text{C}$, $t = 10$ ms)	V_{DSM}/V_{RSM}	$V_{DSM}/V_{RSM} + 100$	V
Peak Gate Current ($T_J = 125^\circ\text{C}$, $t = 20$ ms)	I_{GM}	4.0	W
Peak Gate Power (Pulse Width ≤ 1.0 μs , $T_C = 80^\circ\text{C}$)	P_{GM}	20	W
Average Gate Power ($T_J = 125^\circ\text{C}$)	$P_{G(AV)}$	1.0	W
Operating Junction Temperature Range	T_J	-40 to +125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-40 to +125	$^\circ\text{C}$
RMS Isolation Voltage ($t = 300$ ms, R.H. $\leq 30\%$, $T_A = 25^\circ\text{C}$)	V_{iso}	2500	V

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V_{DRM}^* and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Thermal Characteristics

Rating	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (AC) Junction-to-Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.5 60	$^\circ\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	T_L	260	$^\circ\text{C}$

Electrical Characteristics - OFF ($T_J = 25^\circ\text{C}$ unless otherwise noted ; Electricals apply in both directions)

Characteristic	Symbol	Min	Typ	Max	Unit
Peak Repetitive Blocking Current ($V_D = V_{DRM} = V_{RRM}^*$; Gate Open)	I_{DRM}^* I_{RRM}	-	-	0.005	mA
		-	-	2.0	

Electrical Characteristics - ON ($T_J = 25^\circ\text{C}$ unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Typ	Max	Unit
Forward On-State Voltage (Note 2) ($I_{TM} = \pm 17$ A Peak)	V_{TM}	-	-	1.55	V
Gate Trigger Current (Continuous dc) ($V_D = 12$ V, $R_L = 30$ Ω)	MT2(+), G(+)	2.0	-	35	mA
	MT2(+), G(-)	2.0	-	35	
	MT2(-), G(-)	2.0	-	35	
Holding Current ($V_D = 12$ V, Gate Open, Initiating Current = ± 500 mA)	I_H	-	-	50	mA
Latching Current ($V_D = 12$ V, $I_G = 1.2 \times I_{GT}$)	MT2(+), G(+)	-	-	60	mA
	MT2(+), G(-)	-	-	65	
	MT2(-), G(-)	-	-	60	
Gate Trigger Voltage ($V_D = 12$ V, $R_L = 30$ Ω)	MT2(+), G(+)	0.5	-	1.7	V
	MT2(+), G(-)	0.5	-	1.1	
	MT2(-), G(-)	0.5	-	1.1	
Gate Non-Trigger Voltage ($T_J = 125^\circ\text{C}$)	MT2(+), G(+)	0.2	-	-	V
	MT2(+), G(-)	0.2	-	-	
	MT2(-), G(-)	0.2	-	-	

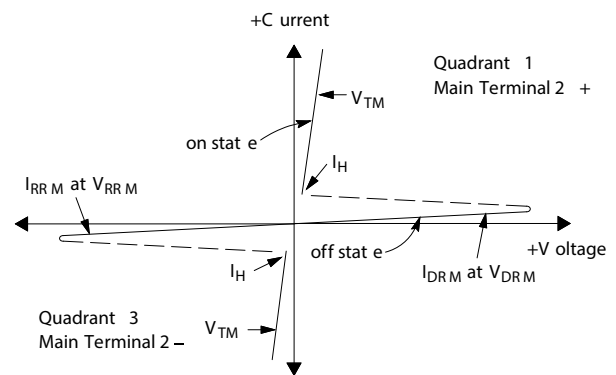
2. Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle $\leq 2\%$.

Dynamic Characteristics

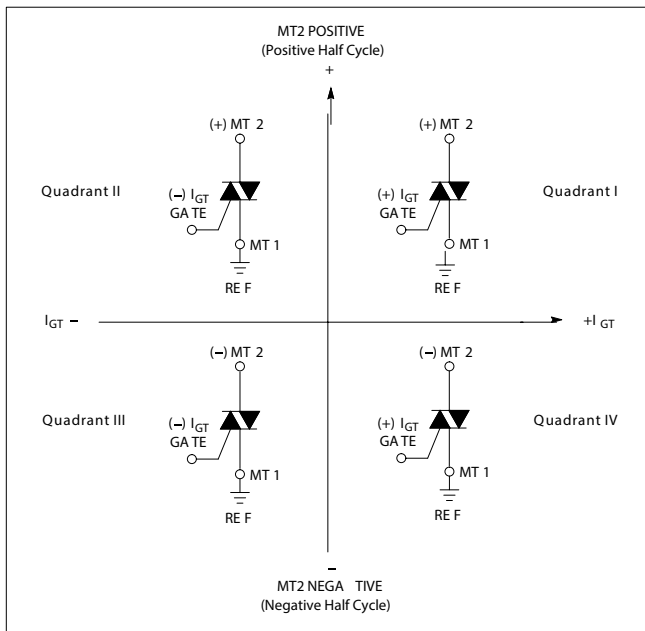
Characteristic	Symbol	Min	Typ	Max	Unit
Rate of Change of Commutating Current, See Figure 9. (Gate Open, $T_j = 125^\circ\text{C}$, No Snubber)	$(di/dt)_c$	8.5	–	–	A/ms
Critical Rate of Rise of On-State Current ($T_j = 125^\circ\text{C}$, $f = 120\text{ Hz}$, $I_g = 2 \times I_{GT}$, $tr \leq 100\text{ ns}$)	di/dt	–	–	50	A/ μs
Critical Rate of Rise of Off-State Voltage ($V_D = 0.66 \times V_{DRM}$, Exponential Waveform, Gate Open, $T_j = 125^\circ\text{C}$)	dV/dt	1000	–	–	V/ μs

Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.
With in-phase signals (using standard AC lines) quadrants I and III are used

Figure 1. RMS Current Derating

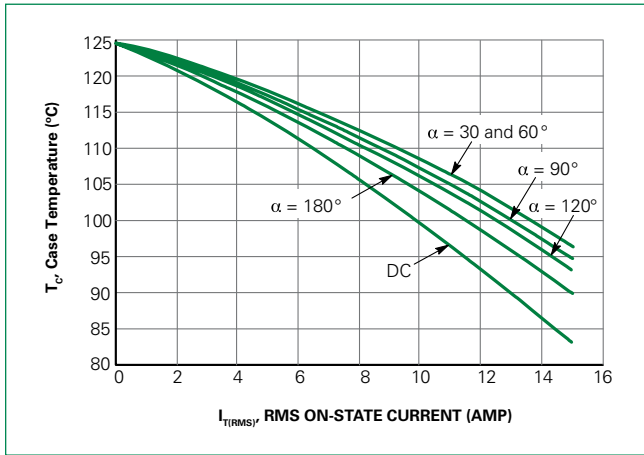


Figure 2. On-State Power Dissipation

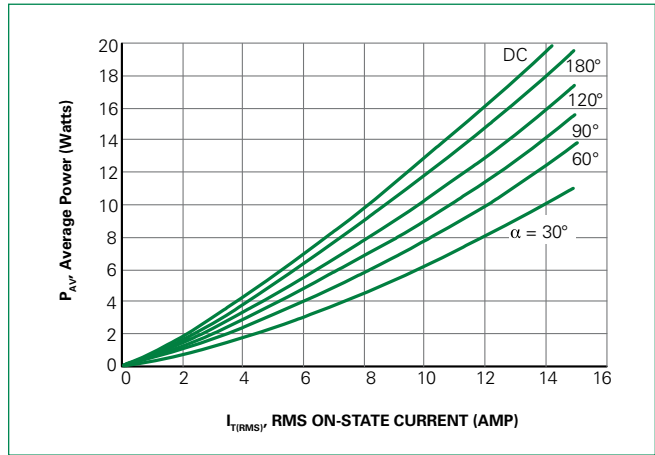


Figure 3. On-State Characteristics

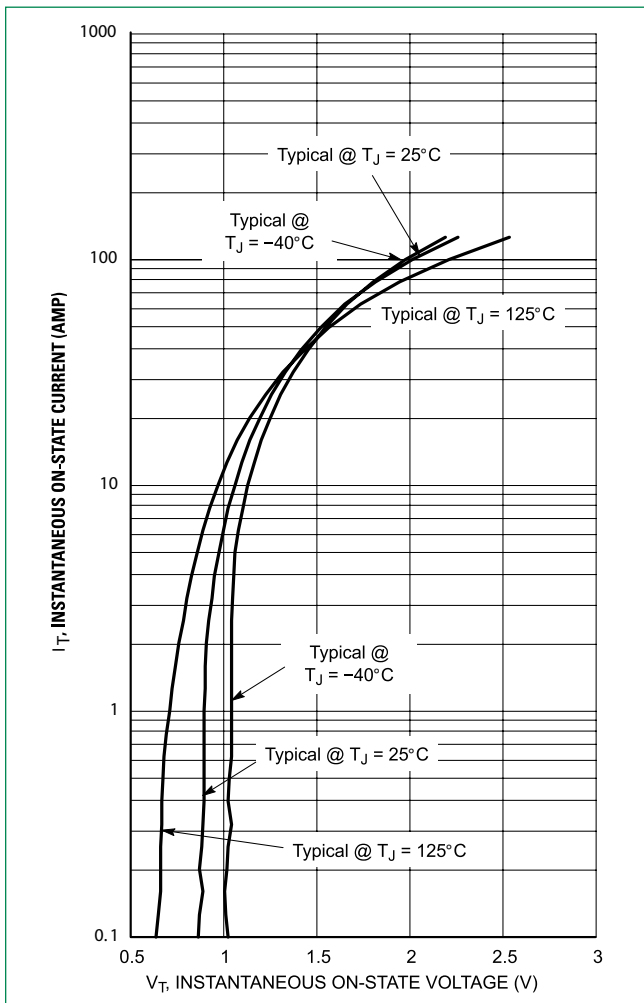


Figure 4. Thermal Response

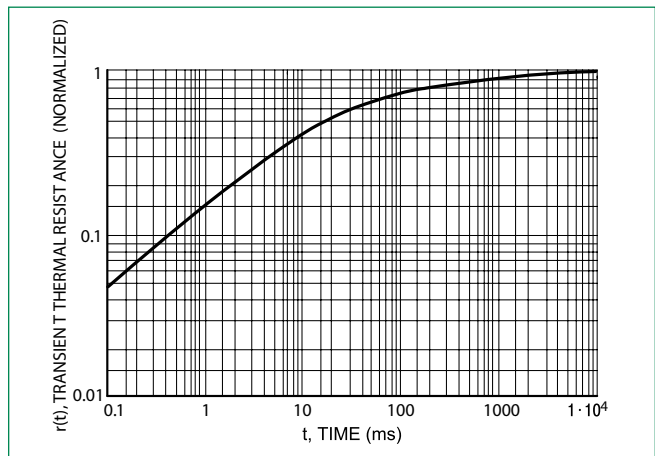


Figure 5. Hold Current Variation

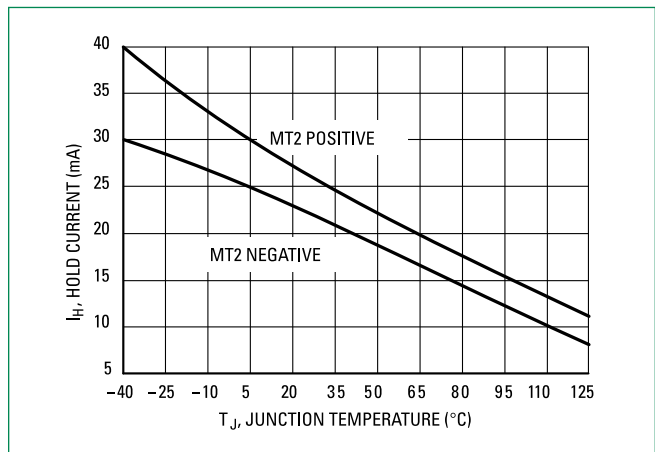


Figure 6. Gate Trigger Current Variation

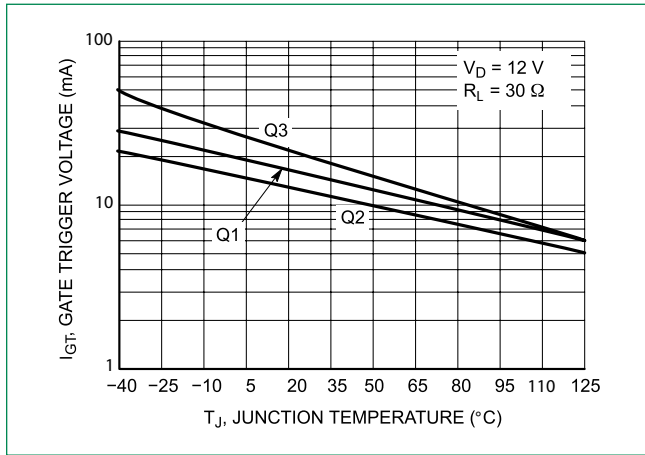


Figure 7. Gate Trigger Voltage Variation

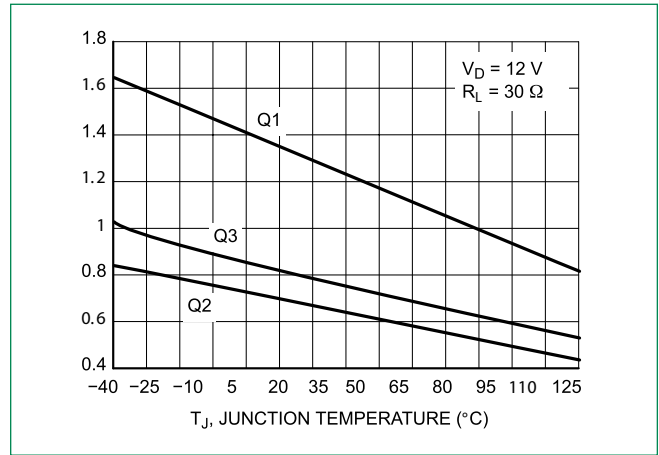
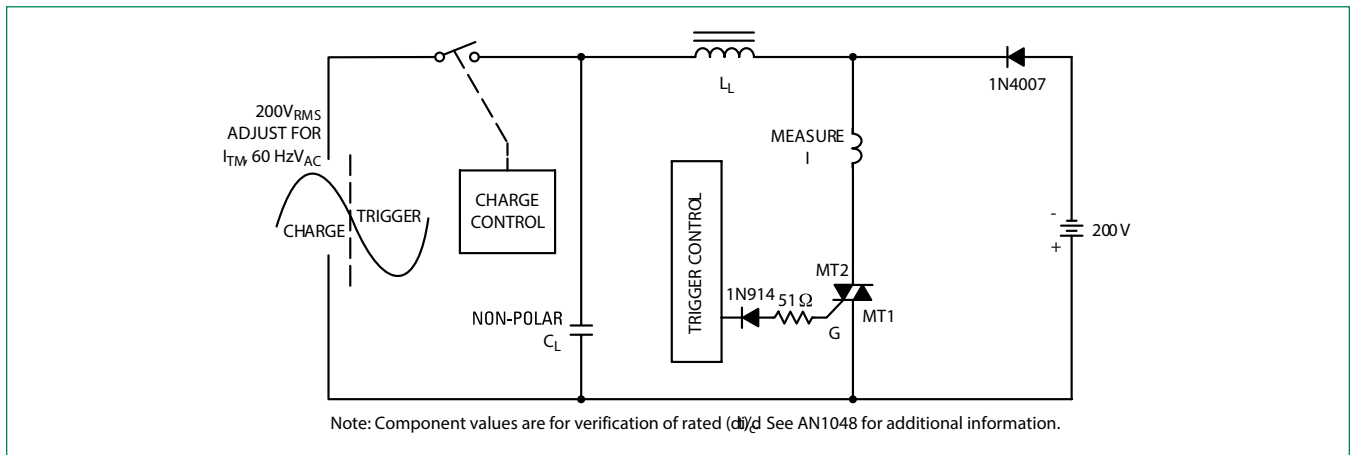


Figure 9. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current (di/dt)



Dimensions

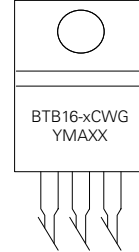


Part Marking System



**TO-220AB
CASE 221A
STYLE 12**

x = 6 or 8
Y = Year
M = Month
A = Assembly Site
XX = Lot Serial Code
G = Pb-Free Package



Dim	Inches		Millimeters	
	Min	Max	Min	Max
A	0.590	0.620	14.99	15.75
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
H	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
K	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
N	0.195	0.205	4.95	5.21
Q	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

Pin Assignment	
1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	No Connection

Ordering Information

Device	Package	Shipping
BTA16-600CW3G	TO-220AB (Pb-Free)	500 Units / Rail
BTA16-800CW3G	TO-220AB (Pb-Free)	500 Units / Rail

Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at <http://www.littelfuse.com/disclaimer-electronics>.

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9